

FDS8958A

Dual N & P-Channel PowerTrench[®] MOSFET

General Description

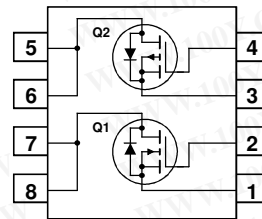
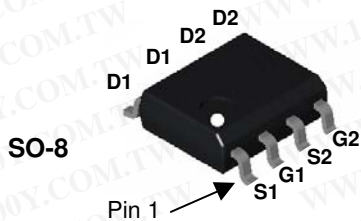
These dual N- and P-Channel enhancement mode power field effect transistors are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.



Features

- **Q1:** N-Channel
 7.0A, 30V $R_{DS(on)} = 0.028\Omega @ V_{GS} = 10V$
 $R_{DS(on)} = 0.040\Omega @ V_{GS} = 4.5V$
- **Q2:** P-Channel
 -5A, -30V $R_{DS(on)} = 0.052\Omega @ V_{GS} = -10V$
 $R_{DS(on)} = 0.080\Omega @ V_{GS} = -4.5V$
- Fast switching speed
- High power and handling capability in a widely used surface mount package



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Q1 | Q2 | Units |
|----------------|--|-------------|----------|------------------|
| V_{DSS} | Drain-Source Voltage | 30 | 30 | V |
| V_{GSS} | Gate-Source Voltage | ± 20 | ± 20 | V |
| I_D | Drain Current - Continuous (Note 1a) | 7 | -5 | A |
| | - Pulsed | 20 | -20 | |
| P_D | Power Dissipation for Dual Operation | 2 | 2 | W |
| | Power Dissipation for Single Operation (Note 1a) | 1.6 | 1.6 | |
| | (Note 1c) | 0.9 | 0.9 | |
| E_{AS} | Single Pulse Avalanche Energy (Note 3) | 54 | 13 | mJ |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a) | 78 | $^\circ\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Note 1) | 40 | $^\circ\text{C/W}$ |

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|----------|-----------|------------|------------|
| FDS8958A | FDS8958A | 13" | 12mm | 2500 units |

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Type | Min | Typ | Max | Units |
|--|--|--|----------|-----------|----------------------------------|----------------------------------|----------------------|
| Off Characteristics | | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ $V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$ | Q1 Q2 | 30 -30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$, Referenced to 25°C $I_D = -250\ \mu\text{A}$, Referenced to 25°C | Q1 Q2 | | 25 -23 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$ | Q1 Q2 | | | 1 -1 | μA |
| I_{GSSF} | Gate-Body Leakage, Forward | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$ | All | | | 100 | nA |
| I_{GSSR} | Gate-Body Leakage, Reverse | $V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$ | All | | | -100 | nA |
| On Characteristics (Note 2) | | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ $V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$ | Q1 Q2 | 1 -1 | 1.9 -1.7 | 3 -3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$, Referenced to 25°C $I_D = -250\ \mu\text{A}$, Referenced to 25°C | Q1 Q2 | | -4.5 4.5 | | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = 10\text{ V}, I_D = 7\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 7\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 4.5\text{ V}, I_D = 6\text{ A}$ $V_{GS} = -10\text{ V}, I_D = -5\text{ A}$ $V_{GS} = -10\text{ V}, I_D = -5\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = -4.5\text{ V}, I_D = -4\text{ A}$ | Q1 Q2 | | 19 27 24 42 57 65 | 28 42 40 52 78 80 | m Ω |
| $I_{D(on)}$ | On-State Drain Current | $V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$ $V_{GS} = -10\text{ V}, V_{DS} = -5\text{ V}$ | Q1 Q2 | 20 -20 | | | A |
| g_{FS} | Forward Transconductance | $V_{DS} = 5\text{ V}, I_D = 7\text{ A}$ $V_{DS} = -5\text{ V}, I_D = -5\text{ A}$ | Q1 Q2 | | 25 10 | | S |
| Dynamic Characteristics | | | | | | | |
| C_{iss} | Input Capacitance | Q1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$ | Q1 Q2 | | 575 528 | | pF |
| C_{oss} | Output Capacitance | Q2 $V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$ | Q1 Q2 | | 145 132 | | pF |
| C_{riss} | Reverse Transfer Capacitance | $V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$ | Q1 Q2 | | 65 70 | | pF |
| R_G | Gate Resistance | $V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$ | Q1 Q2 | | 2.1 6.0 | | Ω |

Electrical Characteristics (continued) $T_A = 25^\circ\text{C}$ unless otherwise noted

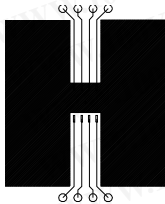
| Symbol | Parameter | Test Conditions | Type | Min | Typ | Max | Units |
|---|---------------------|---|----------|-----|-------------|----------|-------|
| Switching Characteristics (Note 2) | | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | Q1 $V_{DD} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$ | Q1 Q2 | | 8 7 | 16 14 | ns |
| t_r | Turn-On Rise Time | | Q1 Q2 | | 5 13 | 10 24 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | Q2 $V_{DD} = -15\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$ | Q1 Q2 | | 23 14 | 37 25 | ns |
| t_f | Turn-Off Fall Time | | Q1 Q2 | | 3 9 | 6 17 | ns |
| Q_g | Total Gate Charge | Q1 $V_{DS} = 15\text{ V}, I_D = 7\text{ A}, V_{GS} = 10\text{ V}$ | Q1 Q2 | | 11.4 9.6 | 16 13 | nC |
| Q_{gs} | Gate-Source Charge | Q2 | Q1 Q2 | | 1.7 2.2 | | nC |
| Q_{gd} | Gate-Drain Charge | $V_{DS} = -15\text{ V}, I_D = -5\text{ A}, V_{GS} = -10\text{ V}$ | Q1 Q2 | | 2.1 1.7 | | nC |

Drain-Source Diode Characteristics and Maximum Ratings

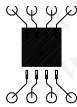
| | | | | | | | |
|----------|--|---|----------|--|---------------|-------------|----|
| I_S | Maximum Continuous Drain-Source Diode Forward Current | | Q1 Q2 | | | 1.3 -1.3 | A |
| I_{SM} | Maximum Pulsed Drain-Source Diode Forward Current (Note 2) | | Q1 Q2 | | | 20 -20 | A |
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = 1.3\text{ A}$ (Note 2) $V_{GS} = 0\text{ V}, I_S = -1.3\text{ A}$ (Note 2) | Q1 Q2 | | 0.75 -0.88 | 1.2 -1.2 | V |
| t_{rr} | Diode Reverse Recovery Time | Q1 $I_F = 7\text{ A}, d_I/d_t = 100\text{ A}/\mu\text{s}$ | Q1 Q2 | | 19 19 | | nS |
| Q_{rr} | Diode Reverse Recovery Charge | Q2 $I_F = -5\text{ A}, d_I/d_t = 100\text{ A}/\mu\text{s}$ | Q1 Q2 | | 9 6 | | nC |

Notes:

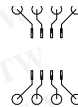
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°/W when mounted on a 0.5 in² pad of 2 oz copper



b) 125°/W when mounted on a .02 in² pad of 2 oz copper



c) 135°/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%
3. Starting $T_J = 25^\circ\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 6\text{ A}$, $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$ (Q1).
Starting $T_J = 25^\circ\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 3\text{ A}$, $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$ (Q2).

Typical Characteristics: Q1 (N-Channel)

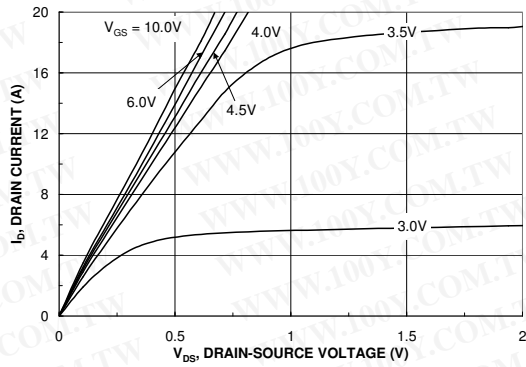


Figure 1. On-Region Characteristics.

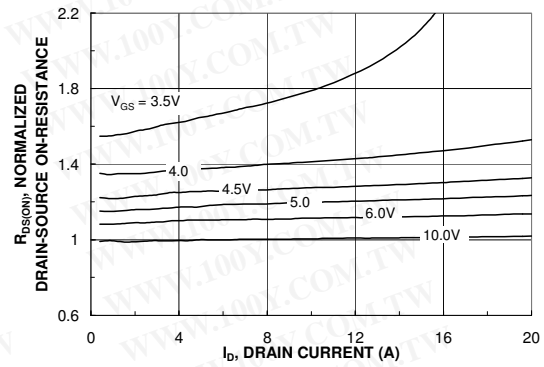


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

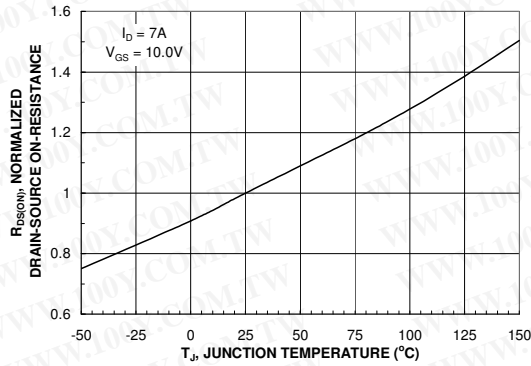


Figure 3. On-Resistance Variation with Temperature.

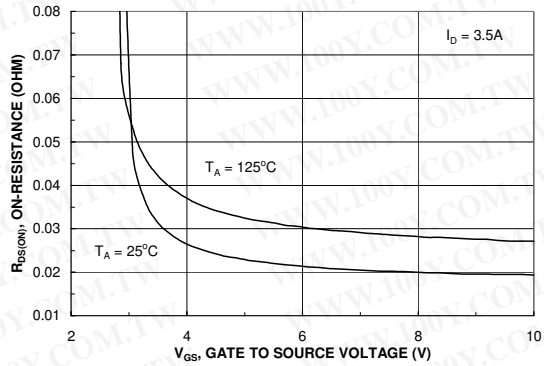


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

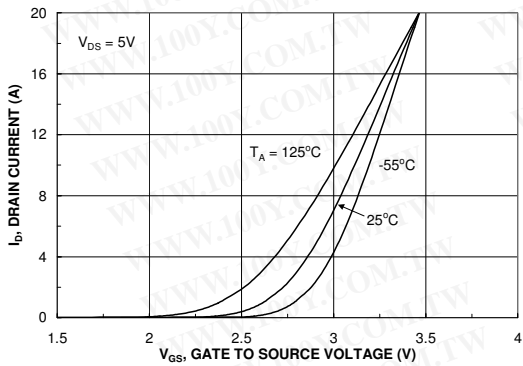


Figure 5. Transfer Characteristics.

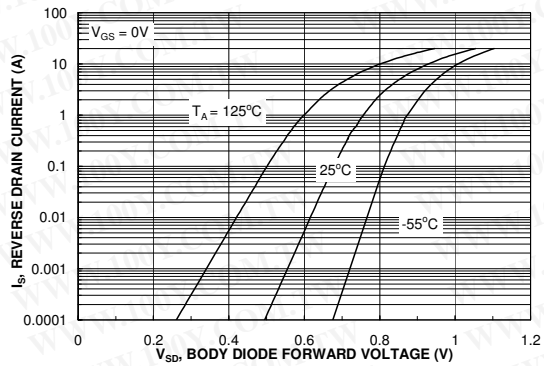


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics: Q1 (N-Channel)

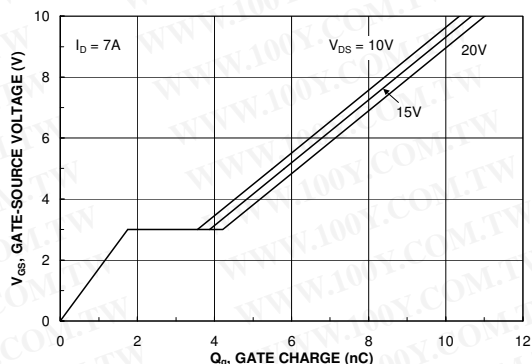


Figure 7. Gate Charge Characteristics.

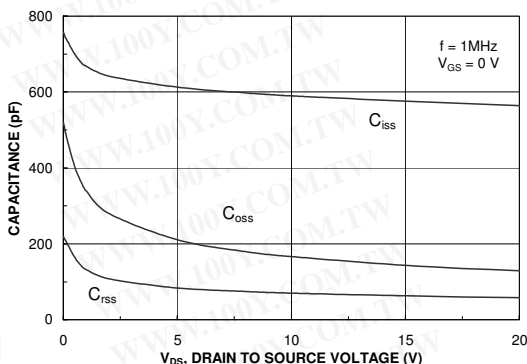


Figure 8. Capacitance Characteristics.

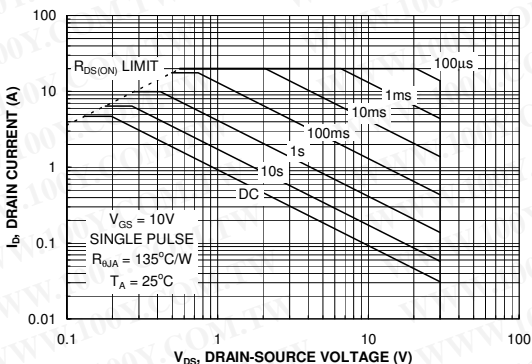


Figure 9. Maximum Safe Operating Area.

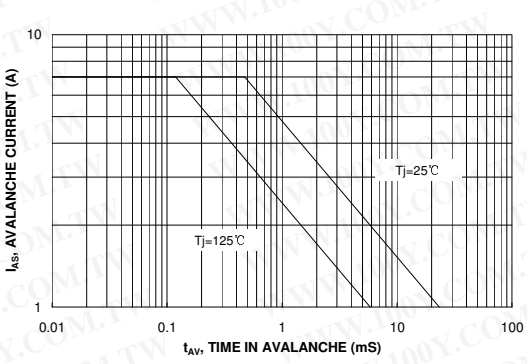


Figure 10. Unclamped Inductive Switching Capability Figure

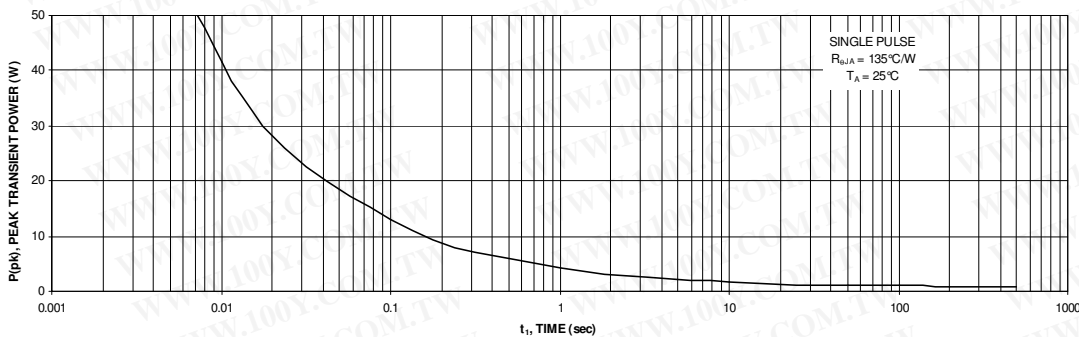


Figure 11. Single Pulse Maximum Power Dissipation.

Typical Characteristics: Q2 (P-Channel)

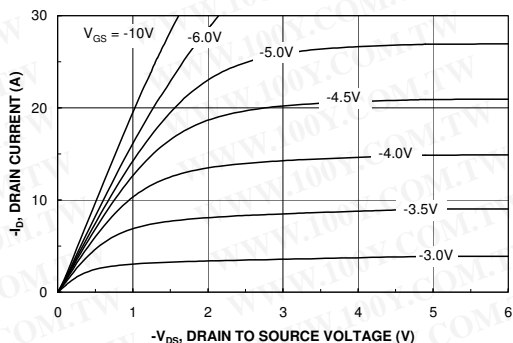


Figure 12. On-Region Characteristics.

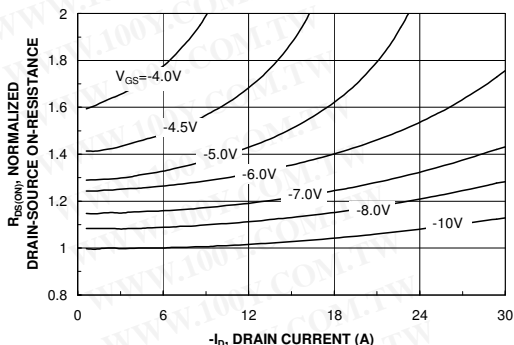


Figure 13. On-Resistance Variation with Drain Current and Gate Voltage.

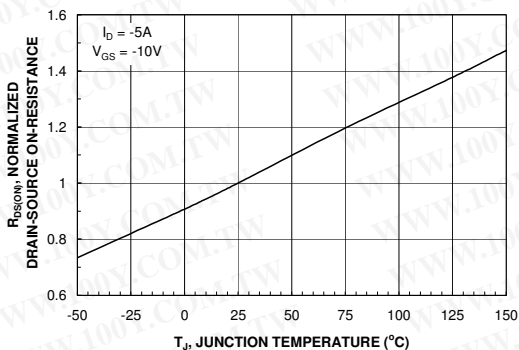


Figure 14. On-Resistance Variation with Temperature.

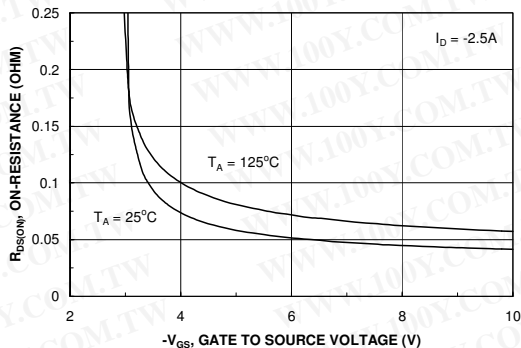


Figure 15. On-Resistance Variation with Gate-to-Source Voltage.

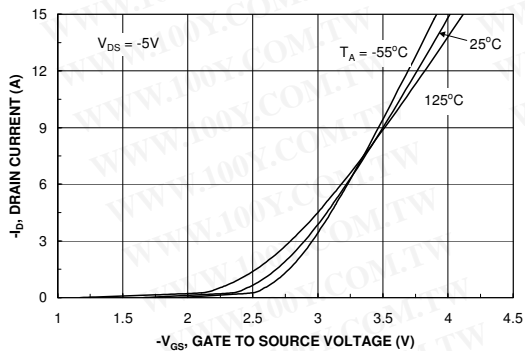


Figure 16. Transfer Characteristics.

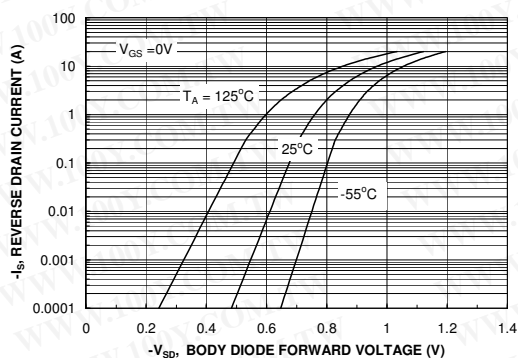


Figure 17. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics: Q2 (P-Channel)

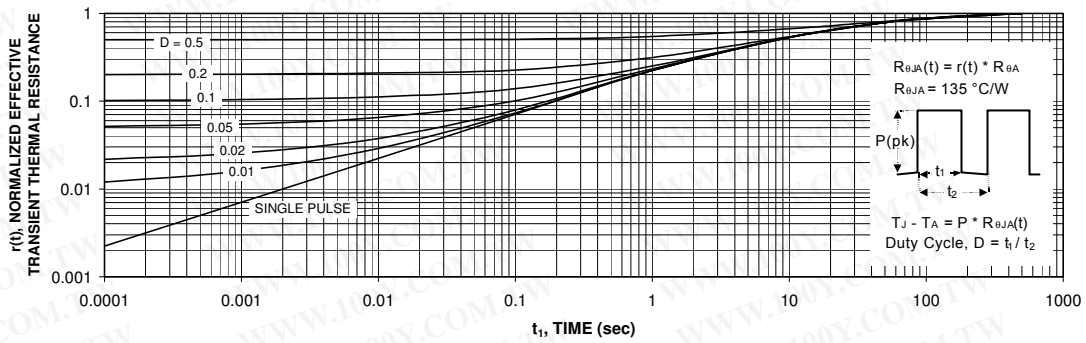


Figure 23. Transient Thermal Response Curve.



Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.



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 - (b) support or sustain life, and
 - (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
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